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74LV139

Dual 2-to-4 line decoder/demultiplexer

Rev. 04 — 13 December 2007 Product data sheet

1. General description

The 74LV139 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC139 and 74HCT139.

The 74LV139 is a dual 2-to-4 line decoder/demultiplexer. It has two independent decoders, each accepting two binary weighted inputs (nA0 and nA1) and providing four mutually exclusive outputs ($n\overline{Y}0$ to $n\overline{Y}3$) that are LOW when selected. Each decoder has an active LOW input ($n\overline{E}$). When $n\overline{E}$ is HIGH, every output is forced HIGH. The enable input can be used as the data input for a 1-to-4 demultiplexer application.

2. Features

- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between V_{CC} = 2.7 V and V_{CC} = 3.6 V
- Typical output ground bounce < 0.8 V at V_{CC} = 3.3 V and T_{amb} = 25 °C
- Typical HIGH-level output voltage (V_{OH}) undershoot: > 2 V at V_{CC} = 3.3 V and T_{amb} = 25 °C
- Demultiplexing capability
- Two independent 2-to-4 line decoders
- Multifunction capability
- Active LOW mutually exclusive outputs
- ESD protection:
  - HBM JESD22-A114E exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LV139N	–40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74LV139D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1

Table 1. Ordering information *...continued*

Type number	Package			
	Temperature range	Name	Description	Version
74LV139DB	−40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74LV139PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74LV139BQ	−40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1

4. Functional diagram

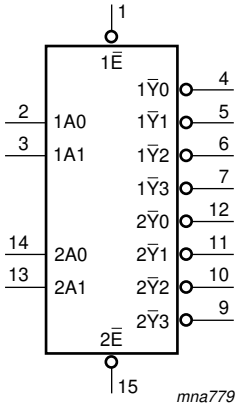
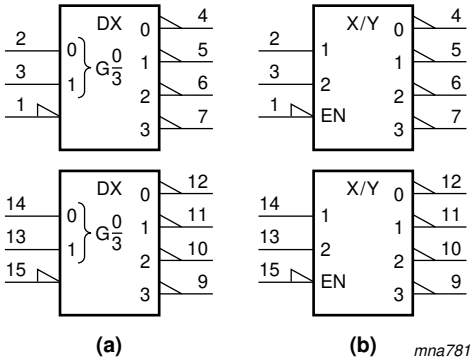


Fig 1. Logic symbol



a) demultiplexer

b) decoder

Fig 2. IEC logic symbol

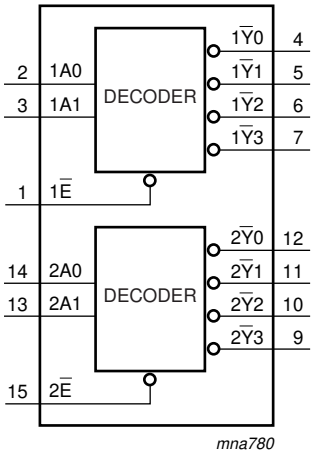


Fig 3. Functional diagram

5. Pinning information

5.1 Pinning

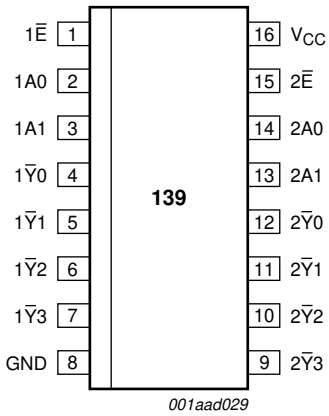
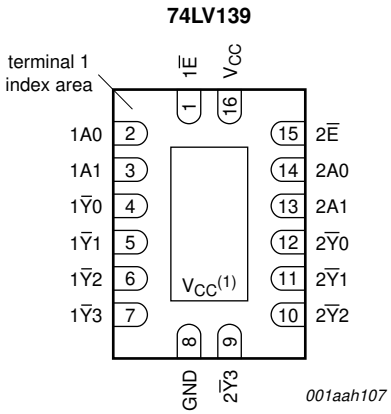


Fig 4. Pin configuration DIP16, SO16 and (T)SSOP16



Transparent top view

(1) The die substrate is attached to this pad using conductive die attach material. It can not be used as a supply pin or input.

Fig 5. Pin configuration DHVQFN16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1Ē	1	enable input (active LOW)
1A0	2	address input
1A1	3	address input
1Y0	4	output
1Y1	5	output
1Y2	6	output
1Y3	7	output
GND	8	ground (0 V)
2Y3	9	output
2Y2	10	output
2Y1	11	output
2Y0	12	output
2A0	14	address input
2A1	13	address input
2Ē	15	enable input (active LOW)
V_{CC}	16	supply voltage

6. Functional description

Table 3. Function table

H = HIGH voltage level; L = LOW voltage level; X = don't care

Input			Output			
$n\overline{E}$	nA0	nA1	$n\overline{Y}0$	$n\overline{Y}1$	$n\overline{Y}2$	$n\overline{Y}3$
H	X	X	H	H	H	H
L	L	L	L	H	H	H
L	H	L	H	L	H	H
L	L	H	H	H	L	H
L	H	H	H	H	H	L

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	-	±50	mA
I_O	output current	$V_O = -0.5$ V to $(V_{CC} + 0.5$ V)		-	±25	mA
I_{CC}	supply current			-	50	mA
I_{GND}	ground current			−50	-	mA
T_{stg}	storage temperature			−65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C				
	DIP16 package		[2]	-	750	mW
	SO16 package		[3]	-	500	mW
	(T)SSOP16 package		[4]	-	500	mW
	DHVQFN16 package		[5]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 12 mW/K above 70 °C.

[3] P_{tot} derates linearly with 8 mW/K above 70 °C.

[4] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[5] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{CC}	supply voltage		[1]	1.0	3.3	5.5	V
V_I	input voltage			0	-	V_{CC}	V
V_O	output voltage			0	-	V_{CC}	V
T_{amb}	ambient temperature			−40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 1.0 V to 2.0 V		-	-	500	ns/V
		V_{CC} = 2.0 V to 2.7 V		-	-	200	ns/V
		V_{CC} = 2.7 V to 3.6 V		-	-	100	ns/V
		V_{CC} = 3.6 V to 5.5 V		-	-	50	ns/V

[1] The static characteristics are guaranteed from V_{CC} = 1.2 V to V_{CC} = 5.5 V, but LV devices are guaranteed to function down to V_{CC} = 1.0 V (with input levels GND or V_{CC}).

9. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level input voltage	V_{CC} = 1.2 V	0.9	-	-	0.9	-	V
		V_{CC} = 2.0 V	1.4	-	-	1.4	-	V
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
		V_{CC} = 4.5 V to 5.5 V	$0.7V_{CC}$	-	-	$0.7V_{CC}$	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.2 V	-	-	0.3	-	0.3	V
		V_{CC} = 2.0 V	-	-	0.6	-	0.6	V
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = −100 µA; V_{CC} = 1.2 V	-	1.2	-	-	-	V
		I_O = −100 µA; V_{CC} = 2.0 V	1.8	2.0	-	1.8	-	V
		I_O = −100 µA; V_{CC} = 2.7 V	2.5	2.7	-	2.5	-	V
		I_O = −100 µA; V_{CC} = 3.0 V	2.8	3.0	-	2.8	-	V
		I_O = −100 µA; V_{CC} = 4.5 V	4.3	4.5	-	4.3	-	V
		I_O = −6 mA; V_{CC} = 3.0 V	2.4	2.82	-	2.2	-	V
		I_O = −12 mA; V_{CC} = 4.5 V	3.6	4.2	-	3.5	-	V

Table 6. Static characteristics *…continued*

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		I_O = 100 µA; V_{CC} = 1.2 V	-	0	-	-	-	V
		I_O = 100 µA; V_{CC} = 2.0 V	-	0	0.2	-	0.2	V
		I_O = 100 µA; V_{CC} = 2.7 V	-	0	0.2	-	0.2	V
		I_O = 100 µA; V_{CC} = 3.0 V	-	0	0.2	-	0.2	V
		I_O = 100 µA; V_{CC} = 4.5 V	-	0	0.2	-	0.2	V
		I_O = 6 mA; V_{CC} = 3.0 V	-	0.25	0.40	-	0.50	V
		I_O = 12 mA; V_{CC} = 4.5 V	-	0.35	0.55	-	0.65	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 5.5 V	-	-	1.0	-	1.0	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	20.0	-	160	µA
ΔI_{CC}	additional supply current	per input; $V_I = V_{CC}$ – 0.6 V; V_{CC} = 2.7 V to 3.6 V	-	-	500	-	850	µA
C_I	input capacitance		-	3.5	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C.

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; For test circuit see Figure 8.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	nAn to n$\overline{Y}$n; see Figure 6 [2]						
		V_{CC} = 1.2 V	-	70	-	-	-	ns
		V_{CC} = 2.0 V	-	24	31	-	39	ns
		V_{CC} = 2.7 V	-	18	23	-	29	ns
		V_{CC} = 3.0 V to 3.6 V; C_L = 15 pF [3]	-	11	-	-	-	ns
		V_{CC} = 3.0 V to 3.6 V [3]	-	13	18	-	23	ns
		V_{CC} = 4.5 V to 5.5 V	-	-	15	-	19	ns
		n$\overline{E}$n to $\overline{Y}$n; see Figure 7						
		V_{CC} = 1.2 V	-	60	-	-	-	ns
		V_{CC} = 2.0 V	-	20	27	-	34	ns
		V_{CC} = 2.7 V	-	15	20	-	25	ns
		V_{CC} = 3.0 V to 3.6 V; C_L = 15 pF [3]	-	10	-	-	-	ns
		V_{CC} = 3.0 V to 3.6 V [3]	-	11	16	-	20	ns
		V_{CC} = 4.5 V to 5.5 V	-	-	13	-	16	ns

Table 7. Dynamic characteristics *...continued*

GND = 0 V; For test circuit see Figure 8.

Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
C_{PD}	power dissipation capacitance	C_L = 50 pF; f_i = 1 MHz; V_I = GND to V_{CC}	[4]	-	42	-	-	-	pF

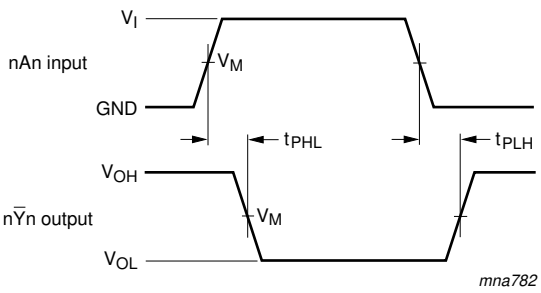
[1] All typical values are measured at T_{amb} = 25 °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V).

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in µW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz, f_o = output frequency in MHz
C_L = output load capacitance in pF
V_{CC} = supply voltage in V
N = number of inputs switching
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

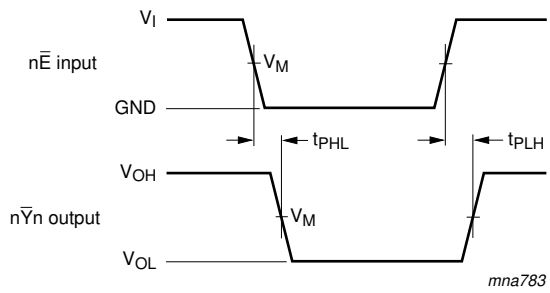
11. Waveforms



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. Input (nAn) to output (nȲn) propagation delays



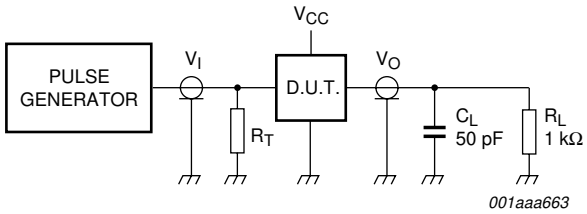
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. Enable input (nĒ) to output (nȲn) propagation delays

Table 8. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
< 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$
2.7 V to 3.6 V	1.5 V	1.5 V
≥ 4.5 V	$0.5V_{CC}$	$0.5V_{CC}$



Test data is given in Table 9.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

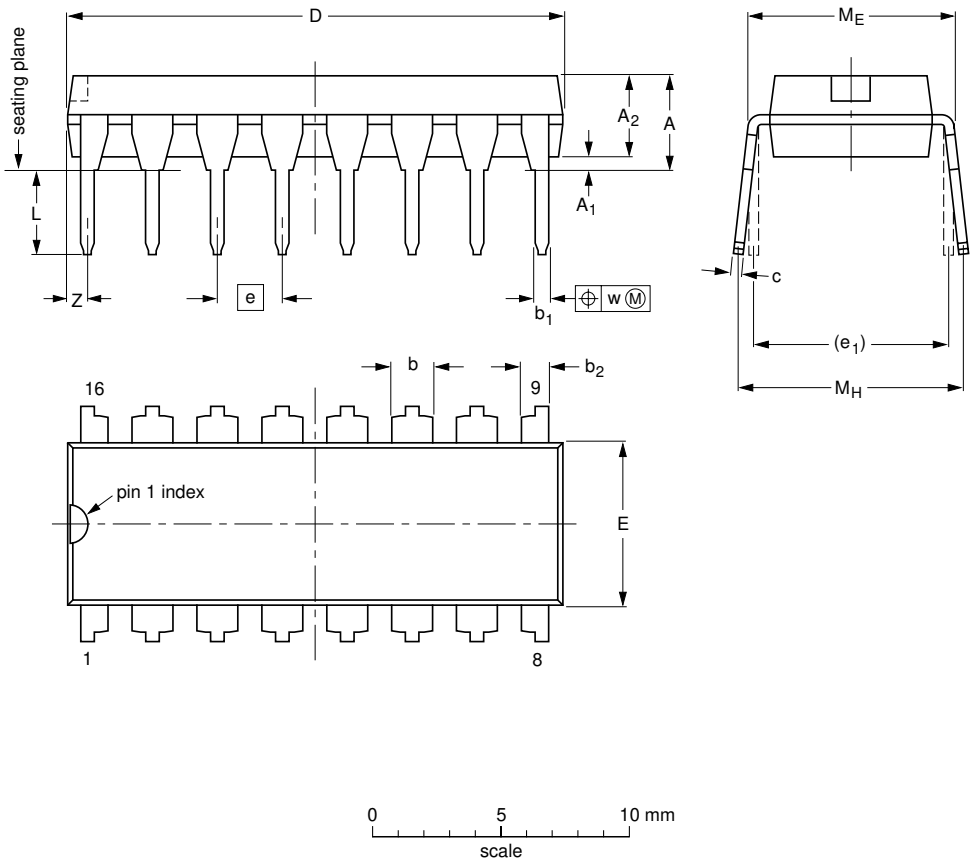
Fig 8. Load circuit for switching times

Table 9. Test data

Supply voltage	Input	
V_{CC}	V_I	t_r, t_f
< 2.7 V	V_{CC}	≤ 2.5 ns
2.7 V to 3.6 V	2.7 V	≤ 2.5 ns
≥ 4.5 V	V_{CC}	≤ 2.5 ns

12. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil) **SOT38-4**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1 min.	A_2 max.	b	b_1	b_2	c	D (1)	E (1)	e	e_1	L	M_E	M_H	w	Z (1) max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

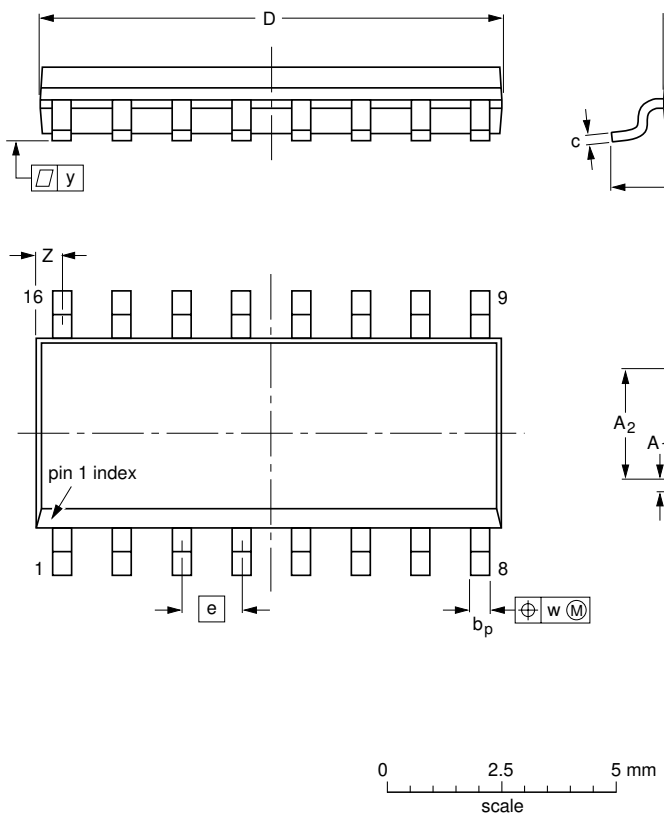
Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT38-4						~~95-01-14~~ 03-02-13

Fig 9. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

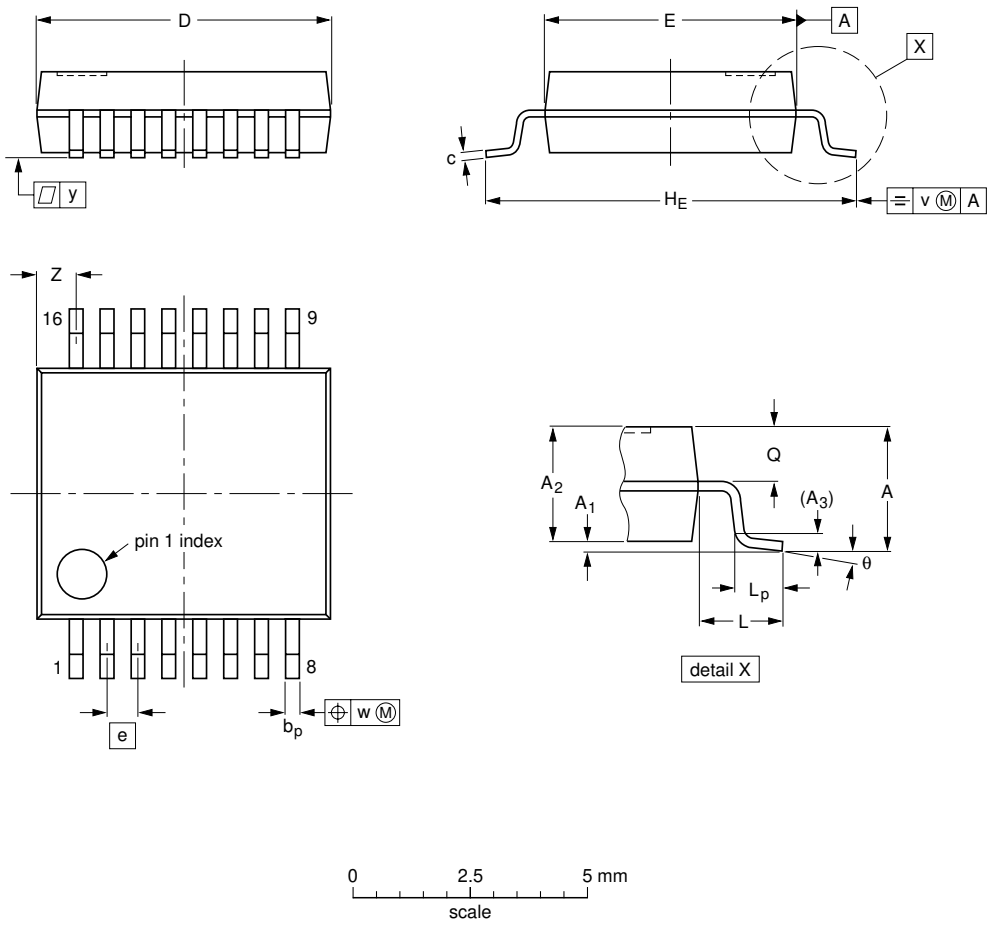
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 10. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm **SOT338-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8^o 0^o

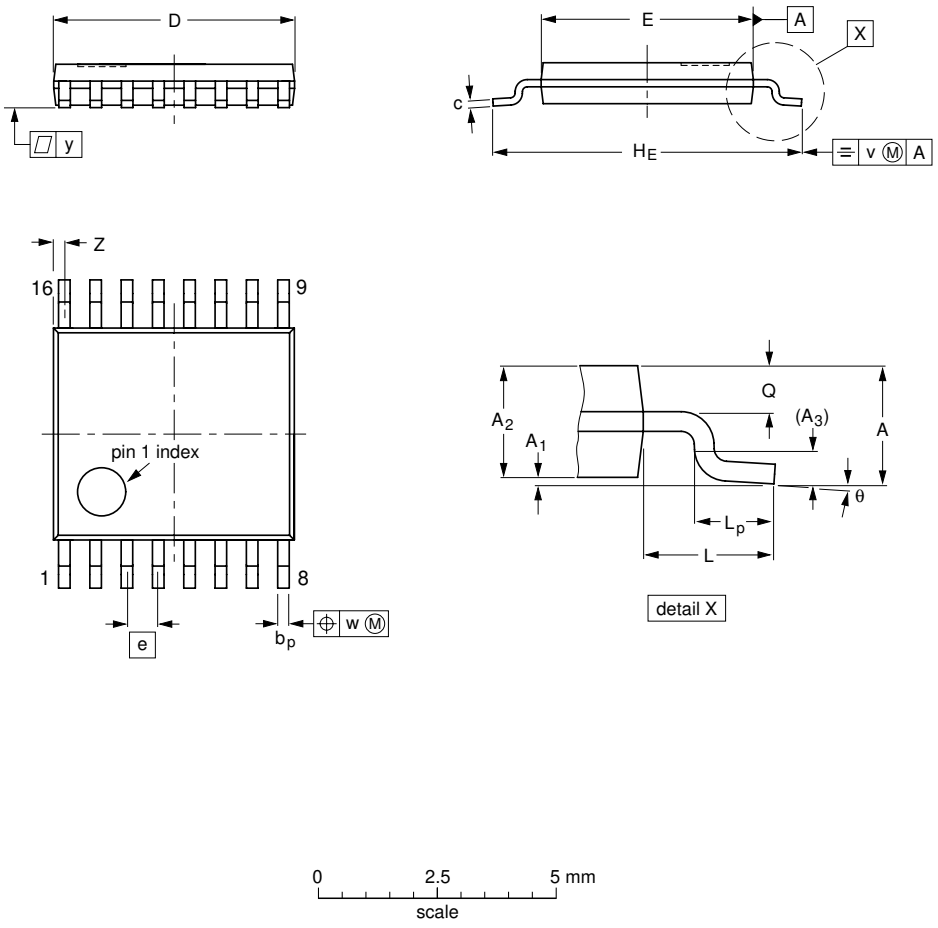
Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT338-1		MO-150				~~99-12-27~~ 03-02-19

Fig 11. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

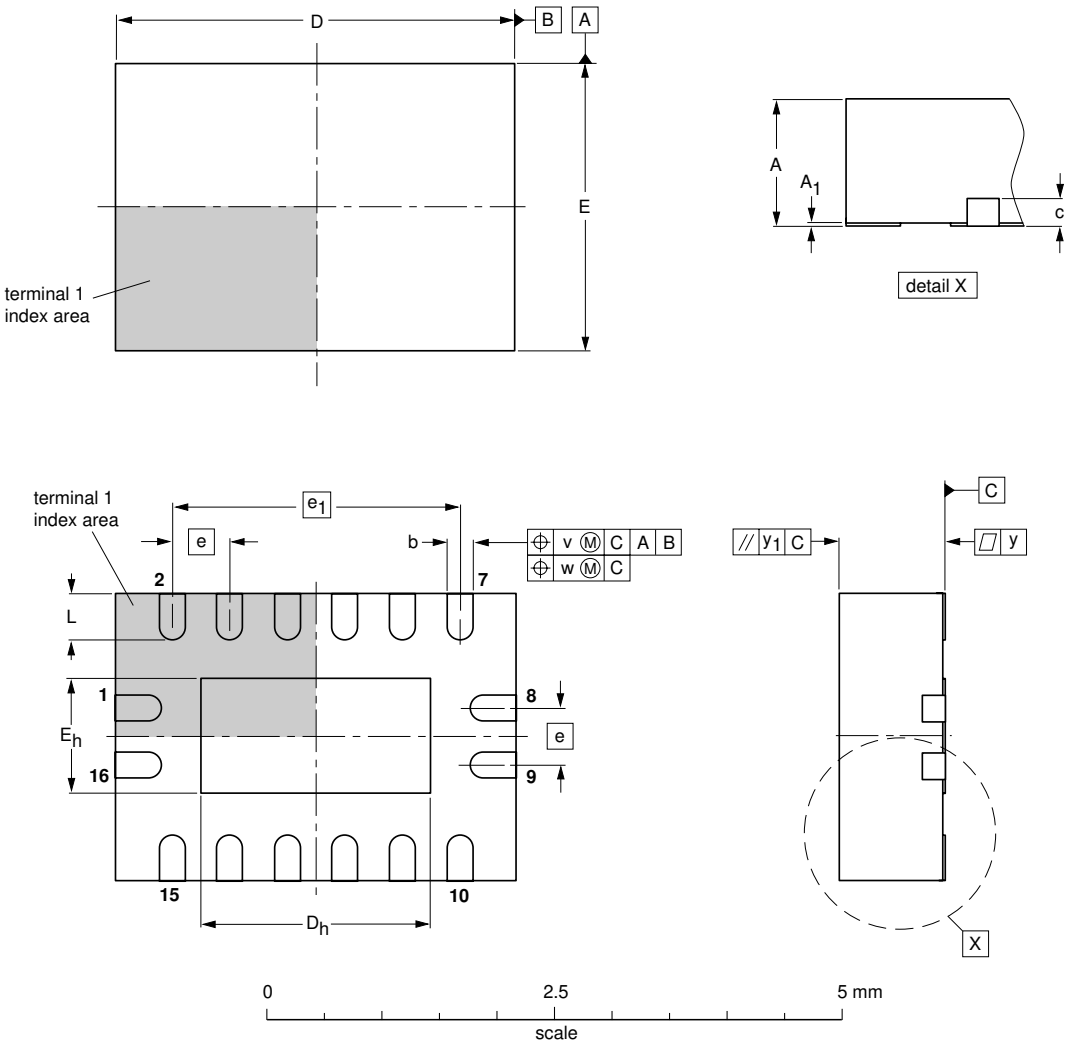
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 12. Package outline SOT403-1 (TSSOP16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm **SOT763-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max.	A_1	b	c	D(1)	D_h	E(1)	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	3.6 3.4	2.15 1.85	2.6 2.4	1.15 0.85	0.5	2.5	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT763-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

Fig 13. Package outline SOT763-1 (DHVQFN16)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LV139_4	20071213	Product data sheet	-	74LV139_3
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Section 3: DHVQFN16 package added. • Section 7: derating values added for DHVQFN16 package. • Section 12: outline drawing added for DHVQFN16 package.			
74LV139_3	20030313	Product specification	-	74LV139_2
74LV139_2	19980428	Product specification	-	74LV139_1
74LV139_1	19970212	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contents

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